



SLPS218C - AUGUST 2009-REVISED APRIL 2010

N-Channel NexFET[™] Power MOSFETs

Check for Samples: CSD16325Q5

FEATURES

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- Optimized for 5V Gate Drive
- Ultralow Q_q and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

APPLICATIONS

- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

DESCRIPTION

The NexFET[™] power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.

Top View 8 s 1] D 2] D S 7 ħр S 3 6 D G D 4 5 DZSC.COM R_{DS(on)} vs V_{GS} 5 R_{DS(on)} - On-State Resistance - mΩ I_D = 30Å 4 = 125°C T_C 3 2 1 25°C C. 0 0 1 2 3 4 5 6 7 8 9 10

V_{GS} - Gate to Source Voltage - V

PRODUCT SUMMARY

-				
V _{DS}	Drain to Source Voltage	25	V	
Qg	Gate Charge Total (4.5V)	18		nC
Q _{gd}	Gate Charge Gate to Drain	3.5		nC
10.	7	$V_{GS} = 3V$	2.1	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$	1.7	mΩ
No.		$V_{GS} = 8V$	1.5	mΩ
V _{GS(th)}	Threshold Voltage	1.1		V

ORDERING INFORMATION

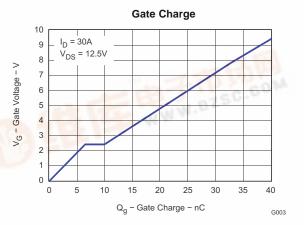
Device Package		Media	Qty	Ship
CSD16325Q5	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5° <mark>C unless o</mark> the <mark>rwise sta</mark> ted	VALUE	UNIT
V _{DS}	Drain to Source Voltage	25	V
V _{GS}	Gate to Source Voltage	+10 /8	V
	Continuous Drain Current, T _C = 25°C	100	А
ID	Continuous Drain Current ⁽¹⁾	33	А
I _{DM}	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	200	А
P_D	Power Dissipation ⁽¹⁾	3.1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	E_{AS} Avalanche Energy, single pulse $I_D = 100A$, L = 0.1mH, R _G = 25 Ω		mJ

(1) Typical $R_{0JA} = 38^{\circ}C/W$ on 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Static C	haracteristics		i.		
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_{D} = 250 \mu A$	25		V
I _{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$		1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$		100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9 1.1	1.4	V
		$V_{GS} = 3V, I_{D} = 30A$	2.1	2.9	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 4.5V, I _D = 30A	1.7	2.2	mΩ
		V _{GS} = 8V, I _D = 30A	1.5	2	mΩ
9 _{fs}	Transconductance	V _{DS} = 15V, I _D = 30A	159		S
Dynamic	c Characteristics			•	
C _{iss}	Input Capacitance		3070	4000	pF
C _{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V,$ f = 1MHz	2190	2850	pF
C _{rss}	Reverse Transfer Capacitance		120	150	pF
R _G	Series Gate Resistance		1.6	3.2	Ω
Qg	Gate Charge Total (4.5V)		18	25	nC
Q _{gd}	Gate Charge – Gate to Drain	V _{DS} = 12.5V,	3.5		nC
Q _{gs}	Gate Charge – Gate to Source	I _{DS} = 30A	6.6		nC
Q _{g(th)}	Gate Charge at Vth		3.3		nC
Q _{oss}	Output Charge	$V_{DS} = 13V, V_{GS} = 0V$	43		nC
t _{d(on)}	Turn On Delay Time		10.5		ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$	16		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 30A, R_G = 2\Omega$	32		ns
t _f	Fall Time		12		ns
Diode C	haracteristics	+			
V _{SD}	Diode Forward Voltage	I _{DS} = 30A, V _{GS} = 0V	0.8	1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = 10V, I _F = 30A, di/dt = 300A/µs	63		nC
t _{rr}	Reverse Recovery Time	V _{DD} = 10V, I _F = 30A, di/dt = 300A/µs	47		ns

THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

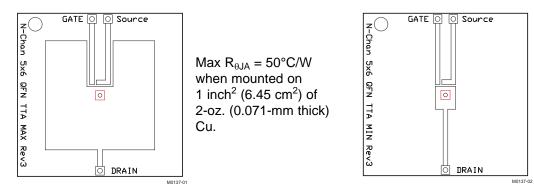
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			1	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾ ⁽²⁾			50	°C/W

(1) R_{θJC} is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.



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Max $R_{\theta,JA} = 126^{\circ}C/W$ when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

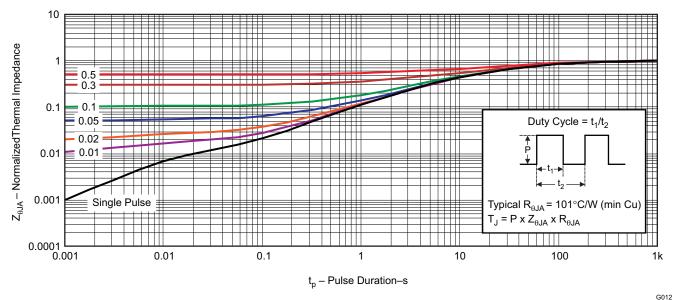


Figure 1. Transient Thermal Impedance

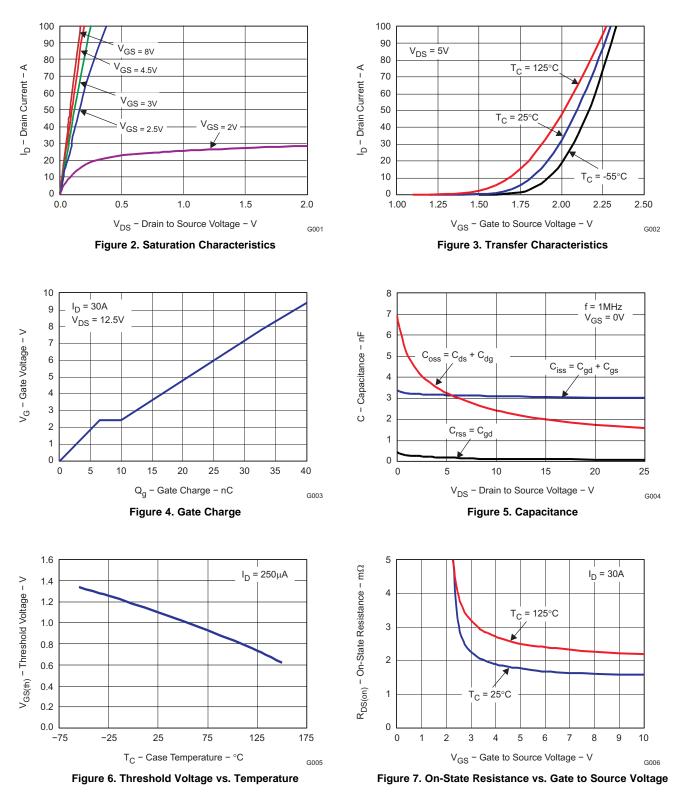
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TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$



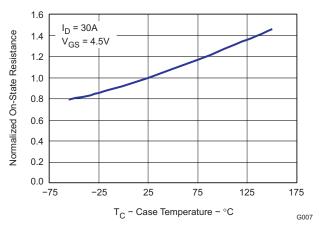


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TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$



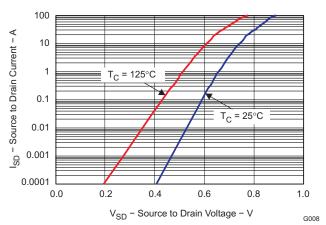


Figure 8. Normalized On-State Resistance vs. Temperature

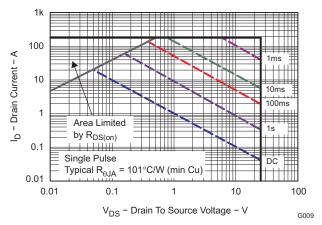


Figure 10. Maximum Safe Operating Area

Figure 9. Typical Diode Forward Voltage

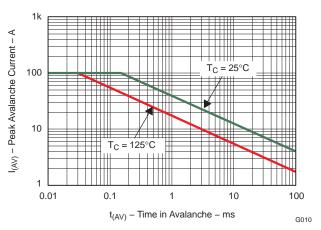
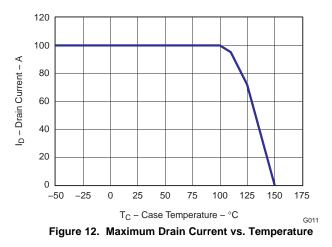


Figure 11. Single Pulse Unclamped Inductive Switching

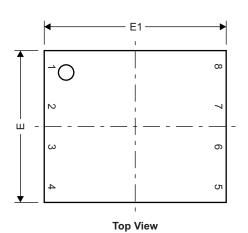


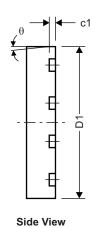
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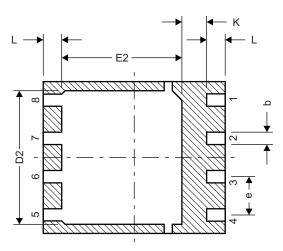
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MECHANICAL DATA

Q5 Package Dimensions







Bottom View



Front View

M0140-01

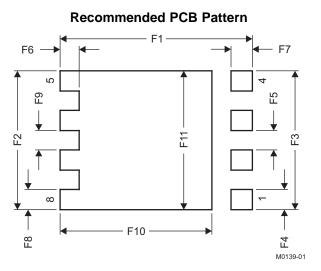
DIM	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
С	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
е	1.27	TYP	0.0)50
L	0.510	0.710	0.020	0.028
θ	0.00			



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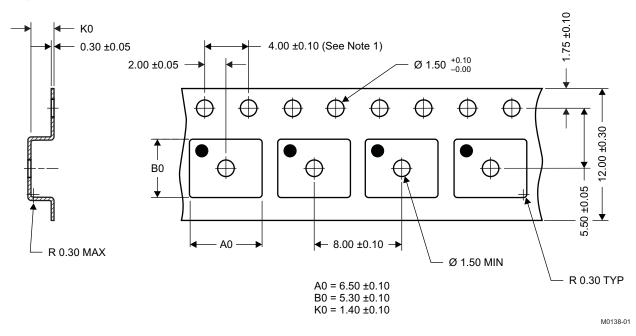
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DIM	MILLIM	IETERS	INC	HES
DIN	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5 Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible

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REVISION HISTORY

Changes from Original (August 2009) to Revision APage• Changed Q_{rr} Reverse Recovery Charge typical value From: 102nC To: 63nC2Changes from Revision A (September 2009) to Revision BPage• Changed Note 1 of the ABSOLUTE MAXIMUM RATINGS From: $R_{0JA} = 38^{\circ}$ C/W To: Typical $R_{0JA} = 38^{\circ}$ C/W1• Changed I_{DM} Pulsed Drain Current in the ABSOLUTE MAXIMUM RATINGS From: 210A To: 200A1• Changed From: Max $R_{0JA} = 48^{\circ}$ C/W To: Max $R_{0JA} = 50^{\circ}$ C/W3• Changed From: Max $R_{0JA} = 48^{\circ}$ C/W To: Max $R_{0JA} = 126^{\circ}$ C/W3• Changed From: Max $R_{0JA} = 101^{\circ}$ C/W To: Typical $R_{0JA} = 101^{\circ}$ C/W3• Changed Figure 1 text - From: $R_{0JA} = 101^{\circ}$ C/W To: Typical $R_{0JA} = 101^{\circ}$ C/W5Changes from Revision B (April 2010) to Revision CPage

•	Changed R _{DS(on)} - V _{GS} = 3V in the Electrical Characteristics table From: 2.7 to 2.9 in the max column	2
•	Deleted the Package Marking Information section	7

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PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Pe
CSD16325Q5	ACTIVE	SON	DQH	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new **PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www. information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retard in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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